

MOSFET - Power, Single P-Channel, SO8-FL

-30 V, 1.8 mΩ, -234 A

NVMFS003P03P8Z

Features

- Ultra Low R_{DS(on)} to Improve System Efficiency
- Advanced Package Technology in 5x6mm for Space Saving and Excellent Thermal Conduction
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- Power Load Switch
- Protection: Reverse Current, Over Voltage, and Reverse Negative Voltage
- Battery Management

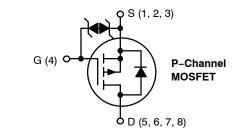
MAXIMUM RATINGS (T_{.J} = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit	
Drain-to-Source Voltage			V_{DSS}	-30	٧
Gate-to-Source Voltage			V_{GS}	± 25	V
Continuous Drain	Steady	, , ,	I _D	-234	Α
Current R _{θJC} (Note 2)	State	T _C = 100°C		-169	
Power Dissipation R _{θJC}		T _C = 25°C	P_{D}	168.7	W
(Note 2)		T _C = 100°C		84.4	
Continuous Drain Cur-	Steady	T _A = 25°C	I _D	-35.7	Α
rent R _{θJA} (Notes 1, 2)	State	T _A = 100°C		-25.7	
Power Dissipation R _{θJA}			P _D	3.9	W
(Notes 1, 2)		T _A = 100°C		1.9	
Pulsed Drain Current	$T_A = 25^{\circ}$	C, $t_p = 10 \mu s$	I _{DM}	-900	Α
Single Pulse Drain-to-Source Avalanche Energy (I _{Lpk} = 37.1 A)			E _{AS}	186	mJ
Operating Junction and Storage Temperature Range			T _J , T _{stg}	-55 to +175	°C
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Surface-mounted on FR4 board using a 1 in² pad size, 2 oz. Cu pad.
- The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

V _{(BR)DSS}	R _{DS(on)}	I _D
-30 V	1.8 mΩ @ –10 V	-234 A
-30 V	2.9 mΩ @ -4.5 V	-204 A



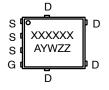


DFN5 5x6, 1.27P (SO-8FL) CASE 488AA



DFNW5 5x6 (FULL-CUT SO8FL WF) CASE 507BA

MARKING DIAGRAM



A = Assembly Location

Y - Year

Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State (Drain) (Note 1)	$R_{\theta JC}$	0.9	°C/W
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	39	°C/W

ELECTRICAL CHARACTERISTICS (T_{.1} = 25°C unless otherwise noted)

Parameter	Symbol	Test Cond	ition	Min	Тур	Max	Unit
OFF CHARACTERISTICS			<u>'</u>		•		
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D =	–250 μΑ	-30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /	I _D = -250 μA, re	of to 25°C		-5		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 \text{ V},$ $V_{DS} = -30 \text{ V}$	T _J = 25°C			-10	μΑ
Gate-to-Source Leakage Current	I _{GSS}	$V_{DS} = 0 V, V_{GS}$	= ±25 V			±10	μΑ
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D =$	-250 μA	-1.0		-3.0	V
Threshold Temperature Coefficient	V _{GS(TH)} /T _J	$I_D = -250 \mu\text{A}, \text{re}$	ef to 25°C		5.5		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = −10 V, I _D	₀ = -23 A		1.2	1.8	mΩ
		V _{GS} = -4.5 V, I _[₀ = -20 A		1.9	2.9	
Froward Transconductance	9FS	$V_{DS} = -5 \text{ V}, I_{D}$	= -20 A		110		S
CHARGES AND CAPACITANCES							
Input Capacitance	C _{iss}	$V_{GS} = 0 \text{ V}, V_{DS} = -15 \text{ V},$			12120		pF
Output Capacitance	C _{oss}	f = 1.0 M	HZ		4020		1
Reverse Transfer Capacitance	C _{rss}				4100		1
Total Gate Charge	Q _{G(TOT)}	$V_{GS} = -4.5 \text{ V}, V_{DS} = -15 \text{ V},$ $I_D = -23 \text{ A}$			167		nC
Threshold Gate Charge	Q _{G(TH)}				7		1
Gate-to-Source Charge	Q _{GS}		-		21		1
Gate-to-Drain Charge	Q_{GD}		-		116		
Total Gate Charge	Q _{G(TOT)}	$V_{GS} = -10 \text{ V}, V_{DS} = -15 \text{ V},$ $I_{D} = -23 \text{ A}$			277		1
SWITCHING CHARACTERISTICS, Vo	is = 4.5 V (Note 3	3)	•				
Turn-On Delay Time	t _{d(on)}	$V_{GS} = -4.5 \text{ V}, V_{D}$	_S = -15 V,		81		ns
Rise Time	t _r	$I_D = -23 \text{ A}, R_0$	$_{\rm G} = 6 \Omega$		440		
Turn-Off Delay Time	t _{d(off)}		-		180		
Fall Time	t _f		-		400		
SWITCHING CHARACTERISTICS, V _G	is = 10 V (Note 3)	•		•		
Turn-On Delay Time	t _{d(on)}	$V_{GS} = -10 \text{ V}, V_{DS}$	_S = -15 V,		28		ns
Rise Time	t _r	$I_D = -23 \text{Å}, R_G = 6 \Omega$			116		1
Turn-Off Delay Time	t _{d(off)}				325		
Fall Time	t _f				380		
DRAIN-SOURCE DIODE CHARACTE	RISTICS						
Forward Diode Voltage	V_{SD}	V _{GS} = 0 V,	T _J = 25°C		-0.75	-1.3	V
		$I_S = -23 A$	T _J = 125°C		-0.6		1

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
DRAIN-SOURCE DIODE CHARACTE	RISTICS	l	<u>I</u>	, ,,		
Reverse Recovery Time	t _{RR}	$V_{GS} = 0 \text{ V, } dl_s/dt = 100 \text{ A/}\mu\text{s,}$ $l_s = -23 \text{ A}$		70		ns
Charge Time	ta	I _S = -23 A		43		
Discharge Time	t _b			28		
Reverse Recovery Charge	Q _{RR}			116		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

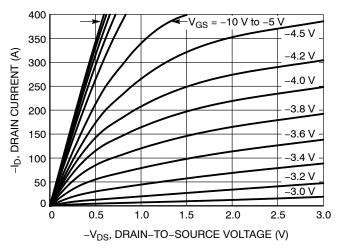


Figure 1. On-Region Characteristics

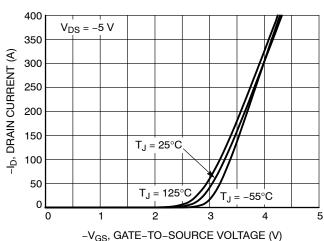


Figure 2. Transfer Characteristics

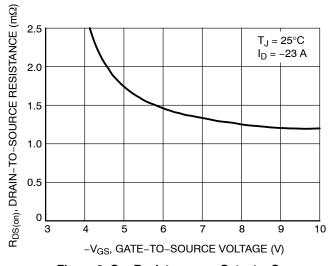


Figure 3. On-Resistance vs. Gate-to-Source Voltage

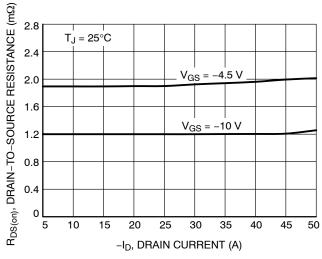


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

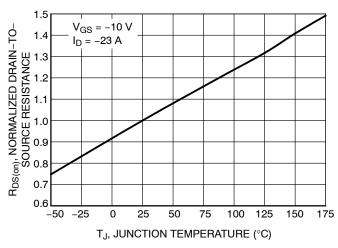


Figure 5. On–Resistance Variation with Temperature

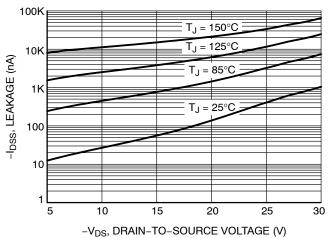


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

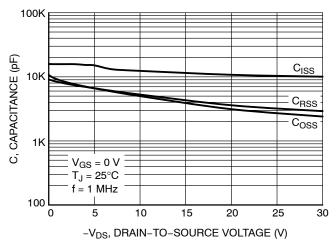


Figure 7. Capacitance Variation

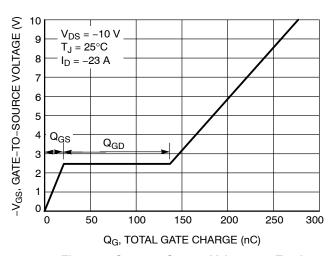


Figure 8. Gate-to-Source Voltage vs. Total Charge

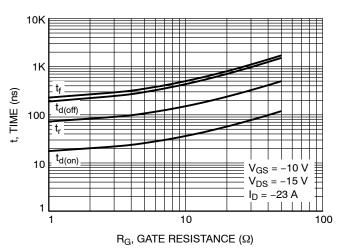


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

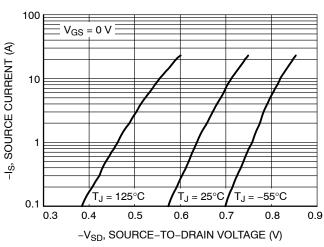


Figure 10. Diode Forward Voltage vs. Current

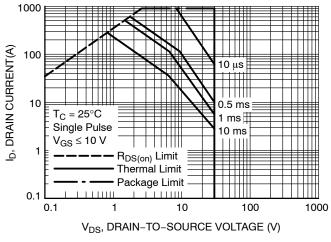


Figure 11. Maximum Rated Forward Biased Safe Operating Area

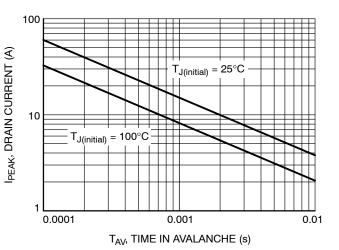


Figure 12. $I_{\mbox{\scriptsize PEAK}}$ vs. Time in Avalanche

TYPICAL CHARACTERISTICS

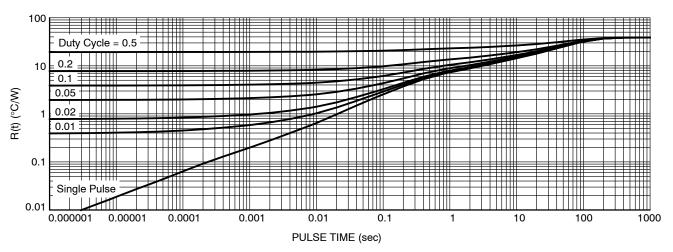


Figure 13. Thermal Characteristics

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping [†]
NVMFS003P03P8ZT1G	03P3	DFN5 5x6, 1.27P (Pb-Free)	1500 / Tape & Reel
NVMFWS003P03P8ZT1G	03P3W	DFNW5, 5x6 (FULL-CUT SO8FL WF) (Pb-Free, Wettable Flanks)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





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SIDE VIEW

DFN5 5x6, 1.27P (SO-8FL) CASE 488AA ISSUE N

DATE 25 JUN 2018

NOTES:

- DIMENSIONING AND TOLERANCING PER
- ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION D1 AND E1 DO NOT INCLUDE
- MOLD FLASH PROTRUSIONS OR GATE BURRS

	MILLIMETERS				
DIM	MIN	NOM	MAX		
Α	0.90	1.00	1.10		
A1	0.00		0.05		
b	0.33	0.41	0.51		
С	0.23	0.28	0.33		
D	5.00	5.15	5.30		
D1	4.70	4.90	5.10		
D2	3.80	4.00	4.20		
E	6.00	6.15	6.30		
E1	5.70	5.90	6.10		
E2	3.45	3.65	3.85		
е		1.27 BSC)		
G	0.51	0.575	0.71		
K	1.20	1.35	1.50		
L	0.51	0.575	0.71		
L1	0.125 REF				
М	3.00	3.40	3.80		
θ	0 °		12 °		

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code

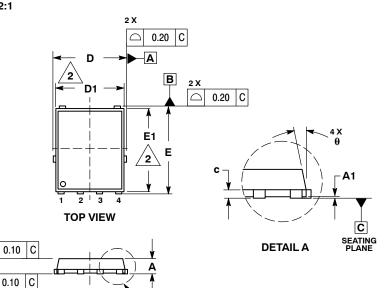
= Assembly Location Α

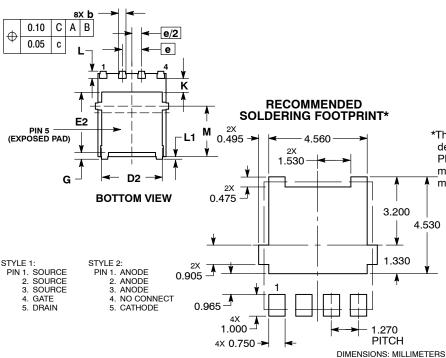
= Lot Traceability

Υ = Year W = Work Week

ZZ

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products may not follow the Generic Marking.





DETAIL A

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98AON14036D	Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	DFN5 5x6, 1.27P (SO-8FL)		PAGE 1 OF 1	

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PIN 1

IDENTIFIER

// 0.10 C

○ 0.10 C



DFNW5 5x6 (FULL-CUT SO8FL WF) CASE 507BA

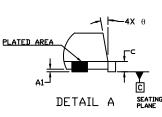
ISSUE A

SEATING PLANE

DATE 03 FEB 2021

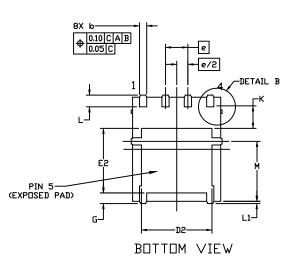


DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
CONTROLLING DIMENSION: MILLIMETERS
DIMENSIONS DI AND EI DO NOT INCLUDE MOLD FLASH,
PROTRUSIONS, OR GATE BURRS.
THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN
FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.



<u> </u>	-4 Χ θ
	_ C
TAIL A	C SEATING PLANE

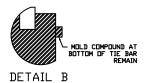
MILLIMETERS DIM MIN. NDM. MAX. 0.90 1.00 1.10 Α 0.05 A1 0.00 0.33 0.41 0.51 b 0.28 0.33 C 0.23 D 5.00 5.15 5.30 D1 4.70 4.90 5.10 D2 3.80 4.00 4.20 Ε 6.00 6.30 6.15 E1 5.70 5.90 6.10 E2 3.45 3.85 3.65 e 1.27 BSC G 0.575 0.71 0.51 1.35 1.50 Κ 1.20 0.575 0.51 0.71 L1 0.150 REF М 3.00 3.40 3.80

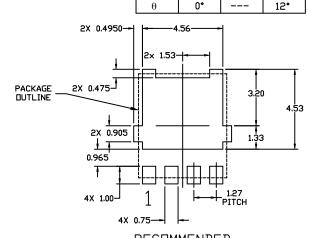


TOP VIEW

SIDE VIEW

DETAIL A





GENERIC MARKING DIAGRAM*



= Assembly Location Α Υ = Year

W = Work Week 77 = Lot Traceability

XXXXXX = Specific Device Code *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present. Some products

may not follow the Generic Marking.

RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

DOCUMENT NUMBER:	98
DOCUMENT NUMBER.	J 30

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DESCRIPTION:

DFNW5 5x6 (FULL-CUT SO8FL WF)

PAGE 1 OF 1

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